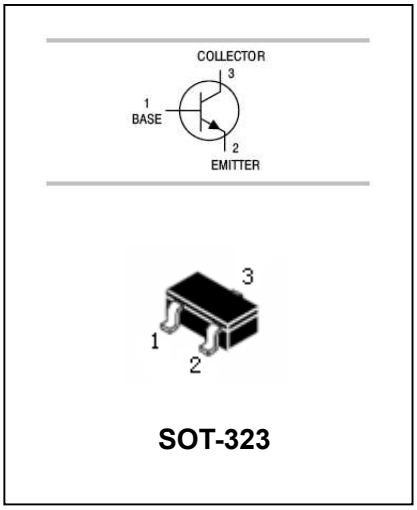
NPN Silicon Epitaxial Planar Transistor 2PD601AW

FEATURES

- Collector Current.(I_C= 100mA)
- Excellent H_{FE} Linearity.
- Power dissipation.(P_C=200mW)

Lead-free



SOT-323

APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2PD601AW	6D/6E/6F	SOT-323

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	**Parameter**	**Value**	**Units**
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector Dissipation	200	mW
T_j,T_{stg}	Junction and Storage Temperature	-55 to +150	℃

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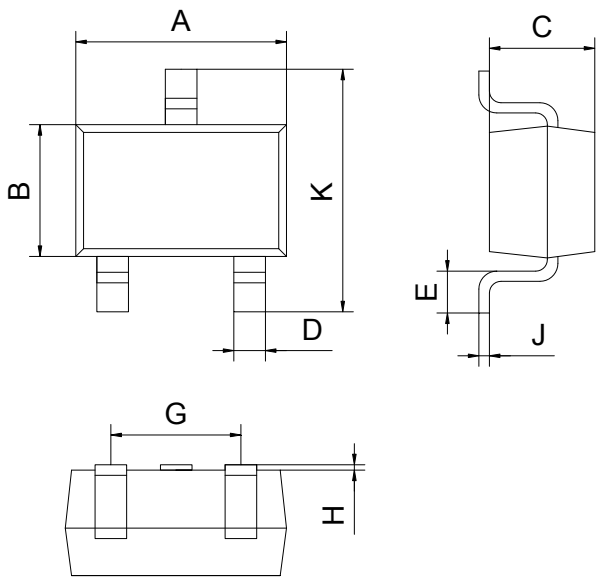
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=60V,I_E=0			0.01	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.01	μA
DC current gain	h_{FE}	V_{CE}=10V,I_C=2mA 2PD601AQW 2PD601ARW 2PD601ASW	 160 210 290		 260 340 460	
		V_{CE}=2V,I_C=100mA	90			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=100mA, I_B= 10mA			0.5	V
Transition frequency	f_T	V_{CE}=6V, I_C= 2mA f=100MHz 2PD601AQW 2PD601ARW 2PD601ASW	 100 120 140			MHz

NPN Silicon Epitaxial Planar Transistor **2PD601AW**

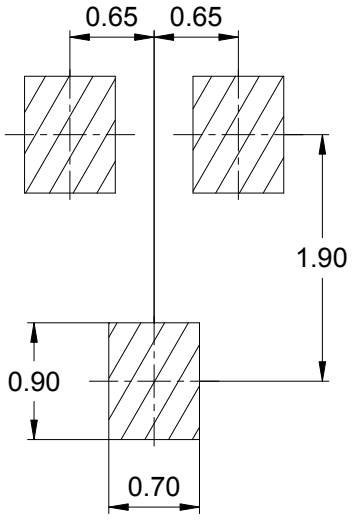
PACKAGE OUTLINE

Plastic surface mounted package SOT-323



SOT-323		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.95 Typical	
D	0.30 Typical	
E	0.25	0.40
G	1.2	1.4
H	0.02	0.10
J	0.10 Typical	
K	2.20	2.40
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit : mm

PACKAGE INFORMATION

Device	Package	Shipping
2PD601AW	SOT-323	3000/Tape&Reel